New Product

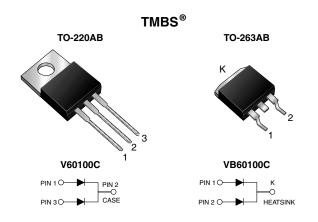


V60100C & VB60100C

Vishay General Semiconductor

Dual High-Voltage Trench MOS Barrier Schottky Rectifier

Ultra Low $V_F = 0.36$ V at $I_F = 5$ A



2 x 30 A

100 V

320 A

0.66 V

150 °C

PRIMARY CHARACTERISTICS

I_{F(AV)}

V_{RRM}

I_{ESM}

 V_F at $I_F = 30$ A

T_{.1} max.

FEATURES

- Trench MOS Schottky technology
- Low forward voltage drop, low power losses



ROHS COMPLIANT

- High efficiency operationLow thermal resistance
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C (for TO-263AB package)
- Solder bath temperature 275 °C maximum, 10 s, per JESD 22-B106 (for TO-220AB)
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC

TYPICAL APPLICATIONS

For use in high frequency converters, switching power supplies, freewheeling diodes, OR-ing diode, dc-to-dc converters and reverse battery protection.

MECHANICAL DATA

Case: TO-220AB and TO-263AB

Molding compound meets UL 94 V-0 flammability rating

Base P/N-E3 - RoHS compliant, commercial grade

Terminals: Matte tin plated leads, solderable per J-STD-002 and JESD 22-B102

E3 suffix meets JESD 201 class 1A whisker test **Polarity:** As marked

Mounting Torque: 10 in-lbs maximum

MAXIMUM RATINGS ($T_A = 25 \text{ °C}$ unless otherwise noted)							
PARAMETER	SYMBOL	V60100C	VB60100C	UNIT			
Maximum repetitive peak reverse voltage	V _{RRM}	100		V			
Maximum average forward rectified current (fig. 1) per device per diode	I _{F(AV)}	60 30		А			
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load per diode	I _{FSM}	320		A			
Non-repetitive avalanche energy at $T_J = 25 \text{ °C}$, L = 140 mH per diode	E _{AS}	450		mJ			
Peak repetitive reverse current at t_p = 2 µs, 1 kHz, T _J = 38 °C ± 2 °C per diode	I _{RRM}	1.0		А			
Voltage rate of change (rated V _R)	dV/dt	10 000		V/µs			
Operating junction and storage temperature range	T _J , T _{STG}	- 40 to + 150		°C			

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ELECTRICAL CHARACTERISTICS (T _A = 25 °C unless otherwise noted)							
PARAMETER	TEST CONDITIONS		SYMBOL	TYP.	MAX.	UNIT	
Breakdown voltage	l _R = 1.0 mA	T _A = 25 °C	V _{BR}	100 (minimum)	-		
Instantaneous forward voltage per diode ⁽¹⁾	I _F = 5 A I _F = 10 A I _F = 15 A I _F = 20 A I _F = 30 A	T _A = 25 °C	V _F	0.45 0.52 0.58 0.63 0.73	- 0.63 - 0.79	V	
	I _F = 5 A I _F = 10 A I _F = 15 A I _F = 20 A I _F = 30 A	T _A = 125 °C		0.36 0.45 0.53 0.58 0.66	- 0.58 - 0.70		
Reverse current at rated V_R per diode ⁽²⁾	V _R = 80 V	T _A = 25 °C T _A = 125 °C	I _R	24 13	500 20	μA mA	
	V _R = 100 V	T _A = 25 °C T _A = 125 °C		65 30	1000 -	μA mA	

Notes

 $^{(1)}$ Pulse test: 300 μs pulse width, 1 % duty cycle

⁽²⁾ Pulse test: Pulse width \leq 40 ms

THERMAL CHARACTERISTICS (T _A = 25 °C unless otherwise noted)						
PARAMETER	SYMBOL	V60100C	VB60100C	UNIT		
Typical thermal resistance per diode	$R_{\theta JC}$	2.5	2.5	°C/W		

ORDERING INFORMATION							
PACKAGE	PREFERRED P/N	UNIT WEIGHT (g)	PACKAGE CODE	BASE QUANTITY	DELIVERY MODE		
TO-220AB	V60100C-E3/4W	1.89	4W	50/tube	Tube		
TO-263AB	VB60100C-E3/4W	1.38	4W	50/tube	Tube		
TO-263AB	VB60100C-E3/8W	1.38	8W	800/reel	Tape and reel		

RATINGS AND CHARACTERISTICS CURVES

(T_A = 25 °C unless otherwise noted)

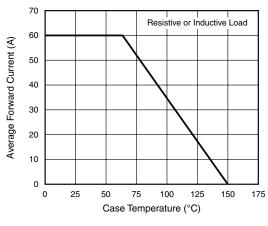


Figure 1. Forward Current Derating Curve

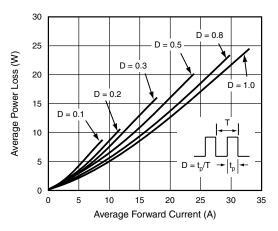


Figure 2. Forward Power Loss Characteristics Per Diode

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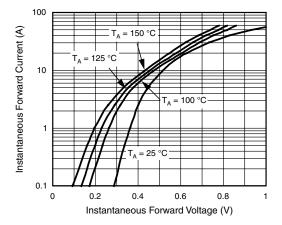


Figure 3. Typical Instantaneous Forward Characteristics Per Diode

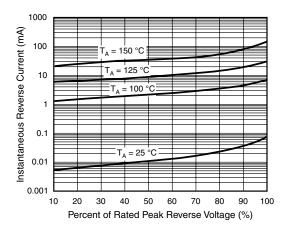


Figure 4. Typical Reverse Characteristics Per Diode

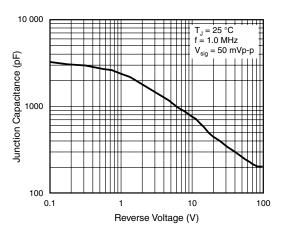


Figure 5. Typical Junction Capacitance Per Diode

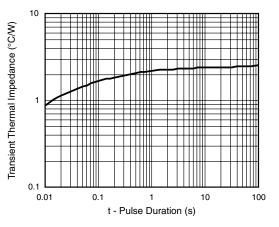


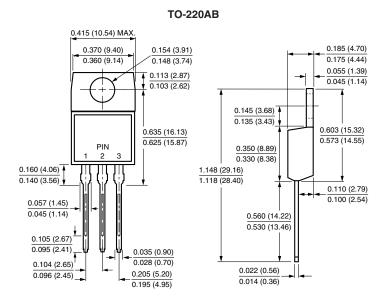
Figure 6. Typical Transient Thermal Impedance Per Diode

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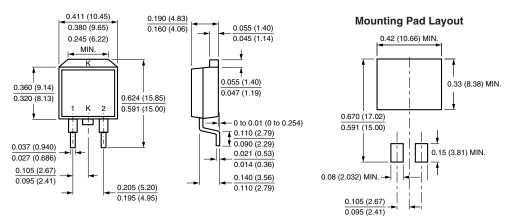
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PACKAGE OUTLINE DIMENSIONS in inches (millimeters)



TO-263AB





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